

What is claimed is:

1 1. A method comprising:
2 soaking a substrate having a dielectric deposited
3 thereon in a salt solution; and
4 depositing an oxide on said dielectric.

1 2. The method of claim 1 wherein depositing an oxide
2 on said dielectric includes depositing aluminum oxide on
3 said dielectric.

1 3. The method of claim 1 wherein soaking said
2 substrate in said salt solution includes soaking said
3 substrate in a salt solution comprising an aluminum salt.

1 4. The method of 3 wherein soaking said substrate in
2 said salt solution comprising said aluminum salt includes
3 soaking said substrate in a salt solution comprising
4 aluminum chloride dissolved in water.

1 5. The method of 3 wherein soaking said substrate in
2 said salt solution comprising said aluminum salt includes
3 soaking said substrate in a salt solution comprising
4 aluminum nitrate dissolved in water.

1 6. The method of claim 3 wherein soaking said
2 substrate in said salt solution comprising said aluminum
3 salt includes causing the reactants in said aluminum salt

4 solution available for surface reaction to range from about
5 a few parts per million to about one percent.

1 7. The method of claim 1 wherein soaking said
2 substrate in said salt solution includes adjusting the pH
3 of said salt solution.

1 8. The method of claim 1 wherein depositing said
2 oxide on said dielectric includes depositing said oxide on
3 silicon dioxide.

1 9. The method of claim 1 wherein depositing said
2 oxide on said dielectric includes depositing said oxide on
3 hafnium oxide.

1 10. The method of claim 1 including depositing a gate
2 material on said oxide.

1 11. A method comprising:
2 preparing a salt solution;
3 exposing a dielectric deposited on a substrate to
4 said salt solution; and
5 causing an oxide to deposit on said dielectric.

1 12. The method of claim 11 wherein preparing said
2 salt solution includes preparing an aluminum salt solution.

1 13. The method of claim 12 wherein preparing said
2 aluminum salt solution includes preparing an aluminum
3 chloride solution.

1 14. The method of claim 12 wherein preparing said
2 aluminum salt solution includes preparing an aluminum
3 nitrate solution.

1 15. The method of claim 12 wherein preparing said
2 aluminum salt solution includes adjusting the pH of said
3 aluminum salt solution.

1 16. The method of claim 12 wherein causing an oxide
2 to deposit on said dielectric includes causing reactants in
3 said aluminum salt solution to react with the top surface
4 of said dielectric.

1 17. The method of claim 16 wherein causing said
2 reactants in said aluminum salt solution to react with the
3 top surface of said dielectric includes depositing an
4 aluminum oxide layer ranging in thickness from about a few
5 parts per million to one or more atomic layers.

1 18. The method of claim 11 wherein exposing said
2 dielectric to said salt solution includes exposing a

3 dielectric selected from the group consisting of silicon
4 dioxide, hafnium dioxide and zirconia to said salt
5 solution.

1 19. The method of claim 11 including removing said
2 substrate from said salt solution and rinsing.

1 20. The method of claim 11 wherein exposing said
2 dielectric to said salt solution includes exposing said
3 dielectric to said salt solution for about a few seconds to
4 about an hour.

1 21. A method comprising:
2 depositing a dielectric on a substrate; and
3 causing an oxide to deposit on said dielectric by
4 immersing said substrate in a salt solution.

1 22. The method of claim 21 wherein depositing a
2 dielectric on said substrate includes depositing an oxide
3 on said substrate.

1 23. The method of claim 22 wherein depositing said
2 oxide on said substrate includes depositing hafnium oxide
3 on said substrate.

1 24. The method of claim 22 wherein depositing said
2 oxide on said substrate includes depositing zirconia on
3 said substrate.

1 25. The method of claim 22 wherein depositing said
2 oxide on said substrate includes depositing silicon dioxide
3 on said substrate.

1 26. The method of claim 21 wherein causing an oxide
2 to deposit on said dielectric by immersing said substrate
3 in a salt solution includes causing aluminum oxide to
4 deposit on said dielectric by immersing said substrate in
5 an aluminum salt solution.

1 27. The method of claim 26 wherein causing said
2 aluminum oxide to deposit on said dielectric includes
3 causing about a few parts per million of aluminum oxide to
4 one or more atomic layers of aluminum oxide to deposit on
5 said dielectric.

1 28. The method of claim 26 including adjusting the pH
2 of said aluminum salt solution.

1 29. The method of claim 26 wherein causing aluminum
2 oxide to deposit on said dielectric by immersing said
3 substrate in said aluminum salt solution includes causing

4 the top surface of said dielectric to react with reactants
5 in said aluminum salt solution.

1 30. The method of claim 21 including a forming a gate
2 material on said oxide.